



ELECTRONICS, INC.
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NTE2593 Silicon NPN Transistor High Voltage Amp/Switch TO-220 Full Pack

Features:

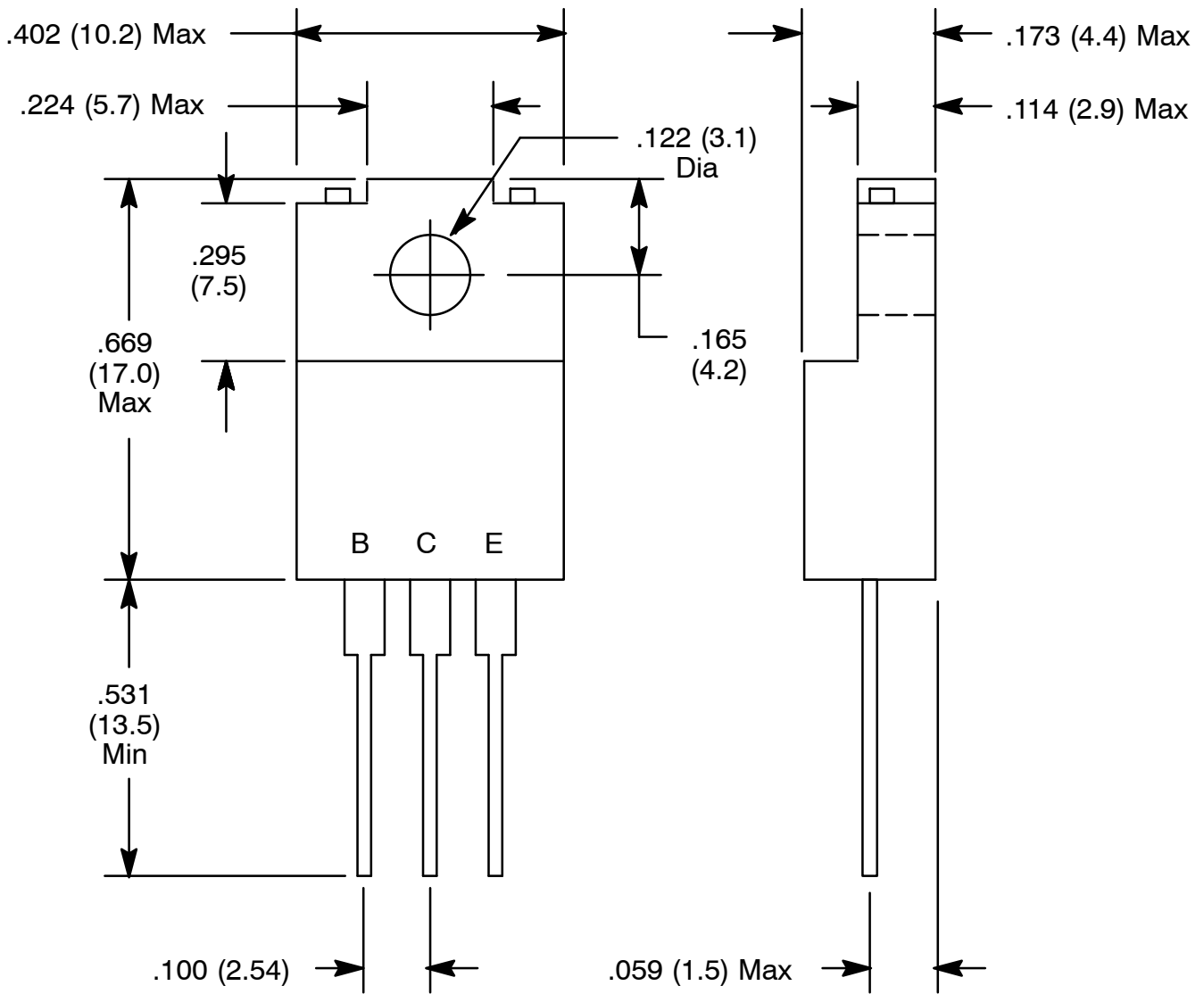
- High Breakdown Voltage: $V_{(BR)CEO} = 2100V$ Min
- Low Output Capacitance
- Wide ASO Range

Absolute Maximum Ratings: ($T_C = +25^{\circ}C$ unless otherwise specified)

| | |
|---|----------------|
| Collector-Base Voltage, V_{CBO} | 2100V |
| Collector-Emitter Voltage, V_{CEO} | 2100V |
| Emitter-Base Voltage, V_{EBO} | 5V |
| Collector Current, I_C | |
| Continuous | 10mA |
| Peak | 30mA |
| Collector Power Dissipation, P_C | 2W |
| Operating Junction Temperature, T_J | +150°C |
| Storage Temperature Range, T_{stg} | -55° to +150°C |

Electrical Characteristics: ($T_C = +25^{\circ}C$ unless otherwise specified)

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|--------------------------------------|---------------|-----------------------------------|------|-----|-----|---------|
| Collector Cutoff Current | I_{CBO} | $V_{CB} = 2100V, I_E = 0$ | - | - | 1 | μA |
| Emitter Cutoff Current | I_{EBO} | $V_{EB} = 4V, I_C = 0$ | - | | 1 | μA |
| DC Current Gain | h_{FE} | $V_{CE} = 5V, I_C = 500\mu A$ | 10 | - | 60 | |
| Gain Bandwidth Product | f_T | $V_{CE} = 10V, I_C = 500\mu A$ | - | 6 | - | MHz |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C = 1mA, I_B = 200\mu A$ | - | - | 5 | V |
| Base-Emitter Saturation Voltage | $V_{BE(sat)}$ | $I_C = 1A, I_B = 200\mu A$ | - | - | 2 | V |
| Collector-Base Breakdown Voltage | $V_{(BR)CBO}$ | $I_C = 10\mu A, I_E = 0$ | 2100 | - | - | V |
| Collector-Emitter Breakdown Voltage | $V_{(BR)CEO}$ | $I_C = 100\mu A, R_{BE} = \infty$ | 2100 | - | - | V |
| Emitter-Base Breakdown Voltage | $V_{(BR)EBO}$ | $I_E = 10\mu A, I_C = 0$ | 5 | - | - | V |
| Output Capacitance | C_{ob} | $V_{CB} = 100V, f = 1MHz$ | - | 1.3 | - | pF |



NOTE: Tab is isolated